

Form 1449*	Atty. Docket No.: 303.459US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: Herewith	Group: Unknown

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>MM</i>	2,842,438	07/08/1958	Saarivirta, M.J., et al.	75	153	08/02/56
	3,954,570	06/04/1976	Shirk, et al.	204	15	11/11/74
	4,386,116	05/31/1983	Nair, et al.	427	99	12/24/81
	4,423,547	01/03/1984	Farrar, P.A., et al.	29	571	06/01/81
	4,574,095	03/04/1986	Baum, et al.	427	53.1	11/19/84
	4,762,728	08/09/1988	Keyser, T., et al.	427	38	11/26/85
	4,788,082	11/29/1988	Schmitt	427	248.1	12/12/85
	4,931,410	06/05/1990	Tokunaga, et al.	437	189	08/25/88
	4,962,058	10/09/1990	Cronin, J.E., et al.	437	187	04/14/89
	4,996,584	02/26/1991	Young, P.L., et al.	357	71	10/13/88
	5,019,531	05/28/1991	Awaya, N., et al.	437	180	05/19/89
	5,100,499	03/31/1992	Douglas, M.A.	156	635	06/25/91
	5,130,274	07/14/1992	Harper, J.M., et al.	437	195	04/05/91
	5,158,986	10/27/1992	Cha, S.W., et al.	521	82	04/05/91
	5,173,442	12/22/1992	Carey, D.H.	437	173	03/24/92
	5,240,878	08/31/1993	Fitzsimmons, J., et al.	437	187	04/26/91
	5,243,222	09/07/1993	Harper, J.M., et al.	257	774	01/08/92
	5,256,205	10/26/1993	Schmitt, III, et al.	118	723	01/07/92
	5,334,356	08/02/1994	Baldwin, D.F., et al.	422	133	08/24/92
	5,354,712	10/11/1994	Ho, Y.Q., et al.	437	195	11/12/92
	5,426,330	06/20/1995	Joshi, R.V., et al.	257	752	09/21/93
	5,442,237	08/15/1995	Hughes, H.G., et al.	257	759	02/04/94
	5,470,789	11/28/1995	Misawa, N.	437	190	03/07/95
	5,470,801	11/28/1995	Kapoor, et al.	437	238	06/28/93
	5,506,449	04/09/1996	Nakano, et al.	257	758	03/23/94
	5,538,922	07/23/1996	Cooper, K.J., et al.	437	195	01/25/95
	5,539,060	07/23/1996	Tsunogae, Y., et al.	525	338	10/13/95
	5,635,253	06/03/1997	Canaperi, et al.	427	437	06/07/95
	5,674,787	10/07/1997	Zhao, et al.	437	230	01/16/96
	5,679,608	10/21/1997	Cheung, et al.	437	195	06/05/95
	5,681,441	10/28/1997	Svendsen, et al.	205	114	12/22/92
	5,695,810	12/09/1997	Dubin, et al.	427	96	11/20/96
	5,739,579	04/14/1998	Chiang, C., et al.	257	635	09/10/96
	5,780,358	07/14/1998	Zhou, M.S.	438	645	04/08/96
	5,785,570	07/28/1998	Bruni, M.D.	445	52	07/25/95
	5,792,522	08/11/1998	Jin, S., et al.	427	575	09/18/96
<i>MM</i>	5,801,098	09/01/1998	Fiordalice, R., et al.	438	653	09/03/96
	5,891,797	04/06/1999	Farrar, P.A.	438	619	10/20/97

Examiner <i>James M. Miller</i>	Date Considered <i>3/18/02</i>
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U.S. PATENT DOCUMENTS

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JMM	5,891,804	04/06/1999	Havemann, R.H., et al.	438	674	04/14/97
JMM	5,897,370	04/27/1999	Joshi, R.V., et al.	438	632	10/28/96
JMM	5,911,113	06/08/1999	Yao, G., et al.	438	649	03/18/97
JMM	5,932,928	08/03/1999	Clampitt, D.A.	257	758	07/03/97
JMM	5,972,804	10/26/1999	Tobin, P.J., et al.	438	786	11/03/97
JMM	5,981,350	11/09/1999	Geusic, J.E., et al.	438	386	05/29/98
JMM	5,985,759	11/16/1999	Kim, E., et al.	438	653	02/24/98
JMM	5,994,777	11/30/1999	Farrar, P.A.	257	758	08/26/98
JMM	6,008,117	12/28/1999	Hong, Q., et al.	438	629	03/19/97
JMM	6,030,877	02/29/2000	Lee, C., et al.	438	381	10/06/97

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

JMM	In: Kirk-Othmer Concise Encyclopedia of Chemical Technology, Grayson, M., (ed.), John Wiley & Sons, Inc., New York, NY, p. 433-435, 926-938, (1985)
JMM	In: Metals Handbook, 8th Edition, Vol. 8, ASM Handbook Committee, (eds.), American Society for Metals, Materials Park, OH, p. 300-302,
JMM	In: Metals Handbook, Ninth Edition, Vol. 2, Properties and Selection: Nonferrous Alloys and Pure Metals, ASM Handbook Committee, (eds.), American Society for Metals, Metals Park, OH, 157, 395, (1989)
JMM	"Brooks Model 5964 High Performance Metal Seal Mass Flow Controller (Introduced in 1991)", Brooks Instrument, http://www.frco.com/brooks/semiconductor/productsli.html , 1 page, (1991)
JMM	Abe, K., et al., "Sub-half Micron Copper Interconnects Using Reflow of Sputtered Copper Films", VLSI Multilevel Interconnection Conference, 308-311, (June 25-27, 1995)
JMM	Andricacos, P.C., "Copper On-Chip Interconnections", The Electrochemical Society Interface, pp. 32-37, (1999)

Examiner <i>JMM</i>	Date Considered <i>3/12/02</i>
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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

JMM	Anonymous, "Formation of Conductors at Variable Depths -- Using Differential Photomask, Projecting Images into Insulator by Reactive Ion Etching, Selectively Filling Images with Conductor", <u>Research Disclosure</u> , Disclosure No. RD 291015, Abstract, 1 p., (July 10, 1988)
	Anonymous, "Improved Metallurgy for Wiring Very Large Scale Integrated Circuits", <u>International Technology Disclosures</u> , 4, Abstract, 1 page, (1986)
	Bae, S., et al., "Low-Temperature Deposition Pathways to Silicon Nitride, Amorphous Silicon, Polycrystalline Silicon, and n type Amorphous Silicon Films Using a High Density Plasma System", <u>IEEE Conference Records---Abstracts, International Conference on Plasma Science</u> , pg. 315, (1997)
	Bai, G., et al., "Copper Interconnection Deposition Techniques and Integration", <u>1996 Symposium on VLSI Technology</u> , Digest of Technical Papers, 48-49, (1996)
	Bernier, M., et al., "Laser processing of palladium for selective electroless copper plating", <u>SPIE</u> , 2045, pp. 330-337, (1994)
	Bhansali, S., et al., "A novel technique for fabrication of metallic structures on polyimide by selective electroless copper plating using ion implantation", <u>Thin Solid Films</u> , 270, pp. 489-492, (1995)
	Bhansali, S., et al., "Selective electroless copper plating on silicon seeded by copper ion implantation", <u>Thin Solid Films</u> , 253, pp. 391-394, (1994)
	Braud, E., et al., "Ultra Thin Diffusion Barriers for Cu Interconnections at The Gigabit Generation and Beyond", <u>VMIC Conference Proceedings</u> , pp. 174-179, (1996)
	Cabrera, A.L., et al., "Oxidation protection for a variety of transition metals and copper via surface silicides formed with silane containing atmospheres", <u>J. Mater. Res.</u> , 6(1), pp. 71-79, (1991)
	Craig, J.D., "Polyimide Coatings", In: <u>Packaging, Electronic Materials Handbook, Vol. 1</u> , ASM International Handbook Committee (eds.), ASM International, Materials Park, OH, 767-772, (1989)
JMM	de Felipe, T.S., et al., "Electrical Stability and Microstructural Evolution in Thin Films of High Conductivity Copper Alloys", <u>IEEE</u> , pp. 293-295, (1999)

Examiner

Date Considered

*Substitute Disclosure Statement Form (PRO-1449)

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

JMA	Ding, et al., "Copper Barrier, Seed Layer and Planerization Technologies", <u>VMIC Conference Proceedings</u> , pp. 87-92, (1997)
	Dubin, V.M., et al., "Selective and Blanket Electroless Copper Deposition for Ultralarge Scale Integration", <u>J. Electrochem. Soc.</u> , 144(3), pp. 898-908, (1997)
	Dushman, S., et al., <u>Scientific Foundations of Vacuum Technique</u> , 2nd Edition, John Wiley and Sons, 1-806, (1962)
	Edelstein, D., et al., "Full Copper Wiring in a Sub-0.25 micrometer CMOS ULSI Technology", <u>IEDM</u> , pp. 773-776, (1997)
	Eldridge, J.M., "New Approaches for Investigating Corrosion in Thin Film Devices", <u>Electronic Packaging and Corrosion in Microelectronics, PROceedings of ASM's Third Conference on Electric Packaging: Materials and Processes & Corrosion in Microelectronics</u> , Mpls, MN, pp. 283-285, (1987)
	Ernst, et al., "Growth Model for Metal Films on Oxide Surface: Cu on ZnO(0001)-O", <u>Physical Review B</u> , 47, 13782-13796, (May 15, 1993)
	Gladfelter, W.L., et al., "Trimethylamine Complexes of Alane as Precursors for the Low-Pressure Chemical Vapor Deposition of Aluminum", <u>Chemistry of Materials</u> , 1, pp. 339-343, (1989)
	Godbey, D.J., et al., "Copper Diffusion in Organic Polymer Resists and Inter-level Dielectrics", <u>Thin Solid Films</u> , 308-309, pp. 470-474, (1997)
	Grimblot, J., et al., "II. Oxidation of Aluminum Films", <u>J. Electrochem.</u> , 129, pp. 2369-2372, (1982)
	Hattangady, S.V., et al., "Integrated processing of silicon oxynitride films by combined plasma and rapid-thermal processing", <u>J. Vac. Sci. Technol. A</u> , 14(6), pp. 3017-3023, (1996)
	Hirao, S., et al., "A Novel Copper Reflow Process Using Dual Wetting Layers", <u>1997 Symposium on VLSI Technology</u> , Digest of Technical Papers, 57-58, (1997)
JMA	Hirata, A., et al., "WSiN Diffusion Barrier Formed by ECR Plasma Nitridation for Copper Damascene Interconnection", <u>16th Solid State Devices and Materials</u> , pp. 260-261, (1998)

Examiner

Date Considered

*Substitute Disclosure Statement Form (#10-1449)

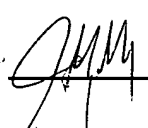

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

	Holloway, K., et al., "Tantalum as a diffusion barrier between copper and silicon", <u>Appl. Phys. Lett.</u> , 57(17), pp. 1736-1738, (October 1990)
	Hu, C.K., et al., "Extendibility of Cu Damascene to 0.1 micrometer Wide Interconnections", <u>Mat. Res. Soc. Symp. Proc.</u> , 514, pp. 287-292, (1998)
	Hymes, S., et al., "Passivation of Copper by Silicide Formation in Dilute Silane", <u>Conference Proceedings ULSI-VII</u> , pp. 425-431, (1992)
	Iijima, T., et al., "Microstructure and Electrical Properties of Amorphous W-Si-N Barrier Layer for Cu Interconnections", <u>1996 VMIC Conference</u> , pp. 168-173, (1996)
	Izaki, M., et al., "Characterization of Transparent Zinc Oxide Films Prepared by Electrochemical Reaction", <u>Journal of the Electrochemical Society</u> , 144, 1949-1952, (June 1997)
	Jayaraj, K., et al., "Low Dielectric Constant Microcellular Foams", <u>Proceedings from the Seventh Meeting of the DuPont Symposium on Polyimides in Microelectronics</u> , pp. 474-501, (September 1996)
	Jeon, Y., et al., "Low-Temperature Fabrication of Polycrystalline Silicon Thin Films by ECR Pecvd", <u>The Electrochemical Society Proceedings</u> , 94(35), pp. 103-114, (1995)
	Jin, C., et al., "Porous Xerogel Films as Ultra-low Permittivity Dielectrics for ULSI Interconnect Applications", <u>Conference Proceedings ULSI XII - 1997 Materials Research Society</u> , pp. 463-469, (1997)
	Kamins, T.I., "Structure and Properties of LPCVD Silicon Films", <u>J. Electrochem. Soc.: Solid-State Science and Technology</u> , 127, pp. 686-690, (March 1980)
	Kang, H.K., et al., "Grain Structure and Electromigration Properties of CVD CU Metallization", <u>Proceedings of the 10th International VLSI Multilevel Interconnection Conference</u> , 223-229, (June 8-9, 1993)
	Keppner, H., et al., "The "Micromorph" Cell: A New Way to High-Efficiency-Low-Temperature Crystalline Silicon Thin-Film Cell Manufacturing", <u>Mat. Res. Soc. Symp. Proc.</u> , 452, pp. 865-876, (1997)

Examiner

Date Considered

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

JMH	Kiang, M., et al., "Pd/Si plasma immersion ion implantation for selective electrless copper plating on Sio2", <u>Appl. Phys. Lett.</u> , 60, pp. 2767-2769, (1992)
	Kistiakowsky, G.B., et al., "Reactions of Nitrogen Atoms. I. Oxygen and Oxides of Nitrogen", <u>The Journal of Chemical Physics</u> , 27(5), pp. 1141-1149, (1957)
	Laursen, T., et al., "Encapsulation of Copper by Nitridation of Cu-Ti Alloy/Bilayer Structures", <u>International Conference on Metallurgical Coatings and Thin Films</u> , Abstract No. H1.03, San Diego, CA, pg. 309, (April 1997)
	Len, V., et al., "An investigation into the performance of diffusion barrier materials against copper diffusion using metal-oxide-semiconductor (MOS) capacitor structures", <u>Solid-State Electronics</u> , 43, pp. 1045-1049, (1999)
	Lyman, T., et al., "Metallography, Structures and Phase Diagrams", <u>Metals Handbook</u> , 8, American Society for Metals, Metals Park, Ohio, pgs. 300 & 302, (1989)
	Marcadal, C., et al., "OMCVD Copper Process for Dual Damascene Metallization", <u>VMIC Conference</u> , ISMIC, pp. 93-97, (1997)
	Miller, R.D., et al., "Low Dielectric Constant Polyimides and Polyimide Nanofoams", <u>Seventh Meeting of the DuPont Symposium on Polyimides in Microelectronics</u> , pp. 443-473, (September 1996)
	Miyake, T., et al., "Atomic Hydrogen Enhanced Reflow of Copper", <u>Applied Physics Letters</u> , 70, 1239-1241, (1997)
	Murarka, S.P., et al., "Copper Interconnection Schemes: Elimination of The Need of Diffusion Barrier/Adhesion Promoter by the Use of Corrosion Resistant, Low Resistivity Doped Copper", <u>SPIE</u> , 2335, pp. 80-90, (1994)
	Nakao, S., et al., "Thin and Low-Resistivity Tantalum Nitride Diffusion Barrier and Giant-Grain Copper Interconnects for Advanced ULSI Metallization", <u>Japanese Journal of Applied Physics</u> , 38(4B), pgs. 262-263, (April 1999)
JMH	Newboe, B., et al., "Applied Materials Announces First Barrier/Seed Layer System For Copper Interconnects", <u>Applied Materials</u> , http://www.appliedmaterials.com/newsroom/pr-00103.html , pgs. 1-4, (1997)

Examiner <i>Jimm M. Ahn</i>	Date Considered <i>3/16/07</i>
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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

JYH	Okamoto, Y., et al., "Magnetically Excited PLasma Oxynitridation of Si at Room Temperature", <u>Jpn. J. Appl. Phys.</u> , 34, pp. L955-957, (1995)
	Palleau, J., et al., "Refractory Metal Encapsulation in Copper Wiring", <u>Advanced Metallization for Devices and Circuits-Science, Technology and Manufacturability, Materials Research Society Symposium Proceedings</u> , 337, pp. 225 - 231, (April 1994)
	Park, C.W., et al., "Activation Energy for Electromigration in Cu Films", <u>Applied Physics Letters</u> , 59(1), 175-177, (July 6, 1991)
	Radzimski, Z.J., et al., "Directional Copper Deposition using d-c Magnetron Self-sputtering", <u>J. Vac. Sci. Technol. B</u> , 16(3), pp. 1102-1106, (1998)
	Ramos, T., et al., "Nanoporous Silica for Dielectric Constant Less Than 2", <u>Conference Proceedings ULSI XII - 1997 Materials Research Society</u> , 455-461, (1997)
	Rath, J.K., et al., "Low-Temperature deposition of polycrystalline silicon thin films by hot-wire CVD", <u>Solar Energy Materials and Solar Cells</u> , 48, pp. 269-277, (1997)
	Ray, S.K., et al., "Flourine-enhanced nitridation of silicon at low temperatures in a microwave plasma", <u>J. Appl. Phys.</u> , 70(3), pp. 1874-1876, (1991)
	Rossnagel, S.M., "Magnetron Sputter Deposition of Interconnect Applications", <u>Conference Proceedings, ULSI XI</u> , 227-232, (1996)
	Rossnagel, S.M., et al., "Metal ion deposition from ionized magnetron sputtering discharge", <u>J. Vac. Sci. Technol. B</u> , 12(1), pp. 449-453, (1994)
	Ryan, J.G., et al., "Copper Interconnects for Advanced Logic and DRAM", <u>Extended Abstracts of the 1998 International Conference on Solid-State Devices and Materials, Hiroshima</u> , pp. 258-259, (1998)
	Ryu, C., et al., "Barriers for copper interconnections", <u>Solid State Technology</u> , pp. 53,54,56, (April 1999)
JYH	Saarivirta, M.J., "High Conductivity Copper Rich Cu-Zr Alloys", <u>Transactions of the Metallurgical Society of AIME</u> , 218, pp. 431-437, (1960)

Examiner

Date Considered

*Substitute Disclosure Statement Form (PFD-1449)

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

JMM	Senzaki, Y., "Chemical Vapor Deposition of Copper using a New Liquid Precursor with Improved Thermal Stability", <u>Conference Proceedings ULSI XIII, Materials Research Society</u> , pp. 451-455, (1998)
	Shacham-Diamand, Y., "100 nm Wide Copper Lines Made by Selective Electroless Deposition", <u>Journal of Micromechanics and Microengineering</u> , 1, 66-72, (March 1991)
	Shacham-Diamond, Y., et al., "Copper electroless deposition technology for ultra-large-scale-integration (ULSI) metallization", <u>Microelectronic Engineering</u> , 33, pp. 47-58, (1997)
	Srivatsa, A.R., et al., "Jet Vapor Deposition: an Alternative to Electrodeposition", <u>Surface Engineering</u> , 11, 75-77, (1995)
	Tao, J., et al., "Electromigration Characteristics of Copper Interconnects", <u>IEEE Electron Devices Letters</u> , 14, 249-251, (May 1993)
	Ting, C.H., "Methods and Needs for Low K Material Research", <u>Materials Research Society Symposium Proceedings, Volume 381, Low-Dielectric Constant Materials -- Synthesis and Applications in Microelectronics</u> , Lu, T.M., et al., (eds.), San Francisco, CA, 3-17, (April 17-19, 1995)
	Tsukada, T., et al., "Adhesion of copper films on ABS polymers deposited in an internal magnet magnetron sputtering system", <u>J. Vac. Sci. Technol.</u> , 16(2), 348-351, (1979)
	Van Vlack, L.H., <u>Elements of Materials Science</u> , Addison-Wesley Publishing Co., Inc. Reading, MA, pg. 468, (1959)
	Venkatesan, S., et al., "A High Performance 1.8V, 0.20 micrometer CMOS Technology with Copper Metalization", <u>IEEE</u> , pp. 769-772, (1997)
	Vossen, J.L., et al., <u>Thin Film Processes II</u> , Academic Press, Inc., 1-866, (1991)
JMM	Wang, K., et al., "Very Low Temperature Deposition of Polycrystalline Silicon Films with Micro-Meter-Order Grains on SiO ₂ ", <u>Mat. Res. Soc. Symp. Proc.</u> , 355, pp. 581-586, (1995)

Examiner

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OTHER DOCUMENTS

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Initial

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JMM	Wang, X.W., et al., "Highly Reliable Silicon Nitride Thin Films Made by Jet Vapor Deposition", <u>Japanese Journal of Applied Physics</u> , 34, 955-958, (February 1995)
	Winters, H.F., et al., "Influence of Surface Absorption Characteristics on Reactivity Sputtered Films Grown in the Biased and Unbiased Modes", <u>J. Appl. Phys.</u> , 43(3), pp. 794-799, (1972)
	Wolf, S., et al., <u>Silicon Processing for the VLSI Era, Vol. 1 -- Process Technology</u> , Lattice Press, Sunset Beach, CA, p. 514-538, (1986)
	Yeh, J.L., et al., "Selective Copper plating of Polysilicon Surface Micromachined Structures", <u>Solid-State Sensor and Actuator Workshop</u> , pp. 248-251, (1998)
JMM	Zhang, J., et al., "Investigations of photo-induced decomposition of palladium acetate for electroless copper plating", <u>Thin Solid Films</u> , 318, pp. 234-238, (1998)

Examiner <i>JMM</i>	Date Considered <i>3/18/02</i>
---------------------	--------------------------------

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